

TSV629x, TSV629xA

Micropower, wide bandwidth CMOS operational amplifiers

Features

- Rail-to-rail input and output
- Low power consumption: 29 μA typ, 36 μA max
- Low supply voltage: 1.5 5.5 V
- High gain bandwidth product: 1.3 MHz typ
- Stable when used in gain configuration
- Low power shutdown mode: 5 nA typ
- Good accuracy: 800 µV max (A version)
- Low input bias current: 1 pA typ
- Micropackages: MiniSO-8, SOT23-8, MiniSO-10, TSSOP14, TSSOP16
- EMI hardened operational amplifiers
- High tolerance to ESD: 4 kV HBM
- Extended temperature range: -40 to +125° C

Applications

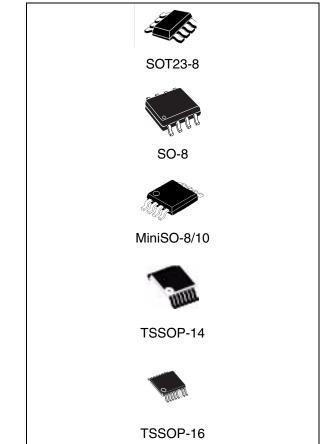
- Battery-powered applications
- Portable devices
- Signal conditioning
- Active filtering
- Medical instrumentation

Description

The TSV6292, TSV6293, TSV6294 and TSV6295 dual and quad operational amplifiers offer a high bandwidth of 1.3 MHz while consuming only 29 μ A. They must be used in a gain configuration (equal or above +4 or -3).

The TSV629x series features low voltage, low power operation and rail-to-rail input and output. The devices also offer an ultra-low input bias current and low input offset voltage.

The TSV6293 (dual) and TSV6295 (quad) have two shutdown pins for reduced power consumption.



These features make the TSV629x family ideal for sensor interfaces, battery supplied and portable applications, as well as active filtering.

Table 1.Device summary

	Dual version		Quad version		
Reference	Without standby	With standby	Without standby	With standby	
TSV629x	TSV6292	TSV6293	TSV6294	TSV6295	
TSV629xA	TSV6292A	TSV6293A	TSV6294A	TSV6295A	

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Package pin connections

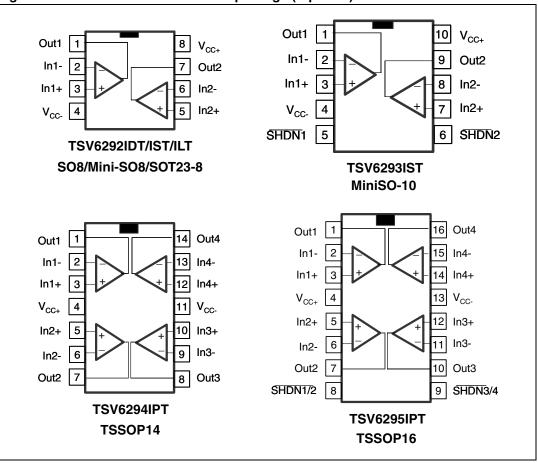


Figure 1. Pin connections for each package (top view)



2 Absolute maximum ratings and operating conditions

Symbol	Parameter	Value	Unit
V _{CC}	Supply voltage ⁽¹⁾	6	V
V _{id}	Differential input voltage ⁽²⁾	±V _{CC}	V
V _{in}	Input voltage ⁽³⁾	V _{CC-} - 0.2 to V _{CC+} + 0.2	V
l _{in}	Input current ⁽⁴⁾	10	mA
SHDN	Shutdown voltage ⁽³⁾	V _{CC-} - 0.2 to V _{CC+} + 0.2	V
T _{stg}	Storage temperature	-65 to +150	°C
R _{thja}	Thermal resistance junction to ambient ⁽⁵⁾⁽⁶⁾ SOT23-8 MiniSO-8 SO-8 Mini-SO10 TSSOP14 TSSOP16	105 190 125 113 100 95	°C/W
Тj	Maximum junction temperature	150	°C
	HBM: human body model ⁽⁷⁾	4	kV
ESD	MM: machine model ⁽⁸⁾	200	V
	CDM: charged device model ⁽⁹⁾	1.5	kV
	Latch-up immunity	200	mA

Table 2. Absolute maximum ratings (AMR)

1. All voltage values, except differential voltages are with respect to network ground terminal.

- 2. Differential voltages are the non-inverting input terminal with respect to the inverting input terminal.
- 3. V_{CC} - V_{in} must not exceed 6 V, V_{in} must not exceed 6V.
- 4. Input current must be limited by a resistor in series with the inputs.
- 5. Short-circuits can cause excessive heating and destructive dissipation.
- 6. Rth are typical values.
- 7. Human body model: 100 pF discharged through a 1.5 k Ω resistor between two pins of the device, done for all couples of pin combinations with other pins floating.
- 8. Machine model: a 200 pF capacitor is charged to the specified voltage, then discharged directly between two pins of the device with no external series resistor (internal resistor < 5 Ω), done for all couples of pin combinations with other pins floating.
- 9. Charged device model: all pins plus package are charged together to the specified voltage and then discharged directly to ground.

Table 3.Operating conditions

Symbol	Parameter	Value	Unit
V _{CC}	Supply voltage	1.5 to 5.5	V
V _{icm}	Common mode input voltage range	V _{CC-} - 0.1 to V _{CC+} + 0.1	V
T _{oper}	Operating free air temperature range	-40 to +125	°C



3 Electrical characteristics

Table 4.Electrical characteristics at $V_{CC+} = +1.8$ V with $V_{CC-} = 0$ V, $V_{icm} = V_{CC}/2$, $T_{amb} = 25^{\circ}$ C,and R_L connected to $V_{CC}/2$ (unless otherwise specified)

Parameter	Conditions		Тур.	Max.	Unit
mance					
Offectuality	TSV629x TSV629xA TSV6293AIST - MiniSO-10			4 0.8 1	mV
Unset voltage	$\begin{split} &TSV629x \cdot T_{min} < T_{op} < T_{max} \\ &TSV629xA \cdot T_{min} < T_{op} < T_{max} \\ &TSV6293AIST \cdot T_{min} < T_{op} < T_{max} \end{split}$			6 2 2.2	
Input offset voltage drift			2		μV/°C
Input offset current			1	10 ⁽¹⁾	pА
I_{io} $(V_{out} = V_{CC}/2)$	T _{min} < T _{op} < T _{max}		1	100	pА
Input bias current			1	10 ⁽¹⁾	pА
$(V_{out} = V_{CC}/2)$	$T_{min} < T_{op} < T_{max}$		1	100	pА
CMR Common mode rejection	0 V to 1.8 V, $V_{out} = 0.9 V$	53	74		dB
ratio 20 log ($\Delta V_{ic}/\Delta V_{io}$)	$T_{min} < T_{op} < T_{max}$	51			dB
Large signal voltage gain	R_L = 10 kΩ, V_{out} = 0.5 V to 1.3 V	78	95		dB
	$T_{min} < T_{op} < T_{max}$	73			dB
High level output voltage	$R_{L} = 10 \text{ k}\Omega$ $T_{min} < T_{op} < T_{max}$	35 50	5		mV
Low level output voltage	$R_L = 10 k\Omega$ $T_{min} < T_{op} < T_{max}$		4	35 50	mV
	V _{out} = 1.8 V	6	12		
Isink	T _{min} < T _{op} < T _{max}	4			mA
-	V _{out} = 0 V	6	10		
Isource	$T_{min} < T_{op} < T_{max}$	4			
	No load, V _{out} =V _{CC} /2		25	31	μA
Supply current (per operator)	T _{min} < T _{op} < T _{max}			33	μA
mance					
Gain bandwidth product	$R_L = 10 \text{ k}\Omega, C_L = 100 \text{ pF}$		1.1		MHz
Minimum gain for stability	Phase margin = 60°, $R_f = 10k\Omega$, $R_L = 10 k\Omega$, $C_L = 20 \text{ pF}$, $T_{op} = 25^\circ \text{ C}$		+4 -3		V/V
Slew rate	$R_L = 10 \text{ k}\Omega$, $C_L = 100 \text{ pF}$, $V_{out} = 0.5 \text{ V}$ to 1.3V		0.33		V/µs
	manceOffset voltageInput offset voltage driftInput offset current $(V_{out} = V_{CC}/2)$ Input bias current $(V_{out} = V_{CC}/2)$ Common mode rejection ratio 20 log $(\Delta V_{ic}/\Delta V_{io})$ Large signal voltage gainHigh level output voltageLow level output voltageIsinkIsourceSupply current (per operator)manceGain bandwidth productMinimum gain for stability	manceTSV629x TSV629xAOffset voltageTSV629xA TSV6293AIST - MiniSO-10TSV629XA - T _{min} < T _{op} < T _{max} TSV6293AIST - T _{min} < T _{op} < T _{max} TSV6293AIST - T _{min} < T _{op} < T _{max} Input offset voltage driftInput offset current (V _{out} = V _{CC} /2)Input bias current (V _{out} = V _{CC} /2)T _{min} < T _{op} < T _{max} Input bias current (V _{out} = V _{CC} /2)0 V to 1.8 V, V _{out} = 0.9 VTmin < T _{op} < T _{max} 0 V to 1.8 V, V _{out} = 0.9 VCommon mode rejection ratio 20 log ($\Delta V_{io}/\Delta V_{io}$)0 V to 1.8 V, V _{out} = 0.5 V to 1.3 VLarge signal voltage gain Timin < T _{op} < T _{max} RL = 10 kQ V _{out} = 0.5 V to 1.3 VHigh level output voltage IsinkRL = 10 kQ T _{min} < T _{op} < T _{max} Usw level output voltage IsinkRL = 10 kQ T _{min} < T _{op} < T _{max} IsourceVout = 0.9Supply current (per operator) Timin < T _{op} < T _{max} No load, V _{out} =V _{CC} /2 T _{min} < T _{op} < T _{max} Bain bandwidth productRL = 10 kQ, CL = 100 pFMinimum gain for stabilityPhase margin = 60°, R _f = 10kQ, RL = 10 kQ, CL = 100 pF, V _{out} = 0.5 V	manceTSV629x TSV6293AIST - MiniSO-10TSV629xA TSV6293AIST - MiniSO-10TSV629xA - Tmin < Top < Tmax TSV6293AIST - Tmin < Top < Tmax TSV6293AIST - Tmin < Top < Tmax TSV6293AIST - Tmin < Top < Tmax Top < Tmax Top < TmaxInput offset voltage driftInput offset voltage driftInput offset current (Vout = V _{CC} /2)OUV to 1.8 V, Vout = 0.9 V53Tmin < Top < TmaxCommon mode rejection ratio 20 log ($\Delta V_{ic}/\Delta V_{io}$)RL = 10 kQ Vout = 0.9 V53Tmin < Top < TmaxCommon mode rejection ratio 20 log ($\Delta V_{ic}/\Delta V_{io}$)RL = 10 kQ Vout = 0.9 V53TomaxInput bias current (Vout = V _{CC} /2)Input bias current (Vout = V _{CC} /2)Input bias current (Vout = V _{CC} /2)TomaxInput bias current (Vout = V _{CC} /2)Input bias current (Vout = 0 kQ Vout = 0.5 V to 1.3 V78Tomax73High level output voltageRL = 10 kQ Vout = 0.5 V to 1.3 V78Tomax10 kQ C Tom < Top < Tmax10 kQ C Tom < Top < Tmax4No load, Vout = 0.5 VInput bias current (Vout = 0 V <td>manceTSV629x TSV629xA TSV6293AIST - MiniSO-10Image: constraint of the system of the s</td> <td>mance TSV629x TSV629xA TSV629xA TSV629xA TSV629xA K 4 Offset voltage $\frac{1}{12}$ $\frac{1}{0}$ $\frac{1}{0}$ $\frac{1}{0}$ Imput offset voltage $\frac{1}{12}$ $\frac{1}{12}$ $\frac{1}{0}$ $\frac{1}{0}$ Input offset voltage drift 2 $\frac{2}{2}$ Input offset current (V_{out} = V_{CC}/2) $\frac{1}{10}$ $\frac{10^{(1)}}{10^{(1)}}$ $\frac{1}{100^{(1)}}$ Input bias current (V_{out} = V_{CC}/2) $\frac{1}{100^{(1)}}$ $\frac{1}{100^{(1)}}$ $\frac{1}{100^{(1)}}$ Input bias current (V_{out} = V_{CC}/2) $\frac{1}{100^{(1)}}$ $\frac{1}{100^{(1)}}$ $\frac{1}{100^{(1)}}$ Common mode rejection ratio 20 log ($\Delta V_{lo}/\Delta V_{lo}$) $\frac{1}{100^{(1)}}$ $\frac{1}{100^{(1)}}$ $\frac{1}{100^{(1)}}$ Large signal voltage gain tain < T_{0p} < T_{max} 51 $\frac{1}{100^{(1)}}$ $\frac{1}{100^{(1)}}$ Large signal voltage for the tot tot ΩC $\frac{1}{100^{(1)} < C_{10} < C_{100} < C_{100}$</td> $\frac{35}{50}$ $\frac{51}{50}$ Low level output voltage $\frac{1}{R_L = 10 k\Omega}$ $\frac{1}{100 k\Omega}$ $\frac{1}{100^{(1)}}$ $\frac{1}{100^{(1)}}$ Isource $\frac{1}{100 k\Omega}$ $\frac{1}{100 k\Omega}$ $\frac{1}{10$	manceTSV629x TSV629xA TSV6293AIST - MiniSO-10Image: constraint of the system of the s	mance TSV629x TSV629xA TSV629xA TSV629xA TSV629xA K 4 Offset voltage $\frac{1}{12}$ $\frac{1}{0}$ $\frac{1}{0}$ $\frac{1}{0}$ Imput offset voltage $\frac{1}{12}$ $\frac{1}{12}$ $\frac{1}{0}$ $\frac{1}{0}$ Input offset voltage drift 2 $\frac{2}{2}$ Input offset current (V _{out} = V _{CC} /2) $\frac{1}{10}$ $\frac{10^{(1)}}{10^{(1)}}$ $\frac{1}{100^{(1)}}$ Input bias current (V _{out} = V _{CC} /2) $\frac{1}{100^{(1)}}$ $\frac{1}{100^{(1)}}$ $\frac{1}{100^{(1)}}$ Input bias current (V _{out} = V _{CC} /2) $\frac{1}{100^{(1)}}$ $\frac{1}{100^{(1)}}$ $\frac{1}{100^{(1)}}$ Common mode rejection ratio 20 log ($\Delta V_{lo}/\Delta V_{lo}$) $\frac{1}{100^{(1)}}$ $\frac{1}{100^{(1)}}$ $\frac{1}{100^{(1)}}$ Large signal voltage gain tain < T _{0p} < T _{max} 51 $\frac{1}{100^{(1)}}$ $\frac{1}{100^{(1)}}$ Large signal voltage for the tot tot ΩC $\frac{1}{100^{(1)} < C_{10} < C_{100} < C_{100} $

1. Guaranteed by design.



able 5.	5. Solution characteristics $v_{CC} = 1.8 v (15v6293, 15v6295)$							
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit		
DC perfo	rmance							
		SHDN = V _{CC-}		2.5	50	nA		
I _{CC}	Supply current in shutdown mode (all operators)	$T_{min} < T_{op} < 85^{\circ} C$			200	nA		
		$T_{min} < T_{op} < 125^{\circ} C$			1.5	μA		
t _{on}	Amplifier turn-on time	$R_L = 5 \text{ k}$, Vout = V_{CC-} to $V_{CC-} + 0.2 \text{ V}$		200		ns		
t _{off}	Amplifier turn-off time	$R_L = 5 \text{ k}$, Vout = $V_{CC+} - 0.5 \text{ V}$ to $V_{CC+} - 0.7 \text{ V}$		20		ns		
V _{IH}	SHDN logic high		1.35			V		
V _{IL}	SHDN logic low				0.6	V		
I _{IH}	SHDN current high	SHDN = V _{CC+}		10		pА		
۱ _{IL}	SHDN current low	SHDN = V _{CC-}		10		pА		
	Output leakage in shutdown	SHDN = V _{CC-}		50		pА		
	mode	T _{min} < T _{op} < 125° C		1		nA		

Table 5. Shutdown characteristics $V_{CC} = 1.8 V$ (TSV6293, TSV6295)

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Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
DC perfo	rmance				I I	
V		TSV629x TSV629xA TSV6293AIST - MiniSO-10			4 0.8 1	
V _{io}	Offset voltage	TSV629x -T _{min} < T _{op} < T _{max} TSV629xA - T _{min} < T _{op} < T _{max} TSV6293AIST - T _{min} < T _{op} < T _{max}			6 2 2.2	mV
$\mathrm{DV}_{\mathrm{io}}$	Input offset voltage drift			2		μV/°C
1	Input offset current			1	10 ⁽¹⁾	pА
I _{io}		$T_{min} < T_{op} < T_{max}$		1	100	pА
	Input bias ourrent			1	10 ⁽¹⁾	pА
l _{ib}	Input bias current	T _{min} < T _{op} < T _{max}		1	100	pА
CMR	Common mode rejection	0 V to 3.3 V, V _{out} = 1.65 V	57	79		dB
CIVIN	ratio 20 log ($\Delta V_{ic}/\Delta V_{io}$)	T _{min} < T _{op} < T _{max}	53			dB
A _{vd}	Large signal voltage gain	R_L =10 k Ω , V_{out} = 0.5 V to 2.8 V	81	98		dB
		T _{min} < T _{op} < T _{max}	76			dB
V _{OH}	High level output voltage		35 50	5		mV
V _{OL}	Low level output voltage	$\begin{aligned} R_L &= 10 \text{ k}\Omega \\ T_{\text{min}} < T_{\text{op}} < T_{\text{max}} \end{aligned}$		4	35 50	mV
	le in le	$V_o = 5 V$	23	45		
	lsink	T _{min} < T _{op} < T _{max}	20			mA
I _{out}		$V_o = 0 V$	23	38		
	Isource	$T_{min} < T_{op} < T_{max}$	20			mA
1	Cupply ourrent (per operator)	No load, V _{out} = 2.5 V		26	33	μA
I _{CC}	Supply current (per operator)	T _{min} < T _{op} < T _{max}			35	μA
AC perfo	rmance					
GBP	Gain bandwidth product	$R_L = 10 \text{ k}\Omega, C_L = 100 \text{ pF}$		1.2		MHz
Gain	Minimum gain for stability	Phase margin = 60°, $R_f = 10k\Omega$, $R_L = 10 k\Omega$, $C_L = 20 pF$, $T_{op} = 25^{\circ} C$		+4 -3		V/V
SR	Slew rate	R_L = 10 kΩ, C_L = 100 pF, V_{out} = 0.5 V to 2.8 V		0.4		V/µs

Table 6. $V_{CC+} = +3.3 \text{ V}$, $V_{CC-} = 0 \text{ V}$, $V_{icm} = V_{CC}/2$, $T_{amb} = 25^{\circ} \text{ C}$, R_L connected to $V_{CC}/2$ (unless otherwise specified)

1. Guaranteed by design.



Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
DC perfo	rmance				L	
		TSV629x TSV629xA TSV6293AIST - MiniSO-10			4 0.8 1	
V _{io}	Offset voltage	$\begin{split} TSV629x &- T_{\min} < T_{op} < T_{\max} \\ TSV629xA &- T_{\min} < T_{op} < T_{\max} \\ TSV629xA &- T_{\min} < T_{op} < T_{\max} \end{split}$			6 2 2.2	mV
DVio	Input offset voltage drift			2		μV/°C
I.	Input offset current			1	10 ⁽¹⁾	pА
l _{io}		T _{min} < T _{op} < T _{max}		1	100	pА
l.,	Input bias current			1	10 ⁽¹⁾	pА
I _{ib}		T _{min} < T _{op} < T _{max}		1	100	pА
CMR	Common mode rejection	0 V to 5 V, $V_{out} = 2.5 V$	60	80		dB
Civin	ratio 20 log ($\Delta V_{ic}/\Delta V_{io}$)	T _{min} < T _{op} < T _{max}	55			
٨	Large signal voltage gain	R_L =10 k Ω , V_{out} = 0.5 V to 4.5 V	85	98		dB
A _{vd}	Large signal voltage gain	T _{min} < T _{op} < T _{max}	80			
SVR	Supply voltage rejection ratio	V _{CC} = 1.8 to 5 V	75	102		dB
341	20 log ($\Delta V_{CC} / \Delta V_{io}$)	T _{min} < T _{op} < T _{max}	73			
		V_{RF} = 100 m V_{rms} , f = 400 MHz		61		
EMIRR	EMI rejection ratio	V _{RF} = 100 mV _{rms} , f = 900 MHz		85		dB
	$EMIRR = -20 \log (V_{RFpeak} / \Delta V_{io})$	V _{RF} = 100 mV _{rms} , f = 1800 MHz		92		uD
		V _{RF} = 100 mV _{rms} , f = 2400 MHz		83		
V _{OH}	High level output voltage	$R_L = 10 \ k\Omega$	35	7		mV
VОН	riigh level output voltage	T _{min} < T _{op} < T _{max}	50			IIIV
Va	Low level output voltage	$R_L = 10 \ k\Omega$		6	35	mV
V _{OL}	Low level output voltage	T _{min} < T _{op} < T _{max}			50	IIIV
	1	$V_0 = 5 V$	40	69		mA
Ι.	lsink	T _{min} < T _{op} < T _{max}	35			
I _{out}		$V_0 = 0 V$	40	74		mA
	Isource	T _{min} < T _{op} < T _{max}	35			
las	Supply current (per operator)	No load, V _{out} = 2.5 V		29	36	μA
I _{CC}	Supply current (per operator)	T _{min} < T _{op} < T _{max}			38	μA

Table 7. $V_{CC+} = +5 V$, $V_{CC-} = 0 V$, $V_{icm} = V_{CC}/2$, $T_{amb} = 25^{\circ} C$, R_L connected to $V_{CC}/2$ (unless otherwise specified)

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Table 7. $V_{CC+} = +5 V$, $V_{CC-} = 0 V$, $V_{icm} = V_{CC}/2$, $T_{amb} = 25^{\circ} C$, R_L connected to $V_{CC}/2$
(unless otherwise specified) (continued)

(
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
AC perfo	rmance					
GBP	Gain bandwidth product	$R_L = 10 \text{ k}\Omega, C_L = 100 \text{ pF}$		1.3		MHz
Gain	Minimum gain for stability	Phase margin = 60°, $R_f = 10k\Omega$, $R_L = 10 k\Omega$, $C_L = 20 pF$, $T_{op} = 25^{\circ} C$		+4 -3		V/V
SR	Slew rate	R_L = 10 kΩ, C_L = 100 pF, V_{out} = 0.5 V to 4.5 V		0.5		V/µs
e _n	Equivalent input noise voltage	f = 1 kHz		77		$\frac{nV}{\sqrt{Hz}}$
THD+N	Total harmonic distortion + noise			0.03		%

1. Guaranteed by design.

Table 8.Shutdown characteristics at V_{CC} = 5 V (TSV6293, TSV6295)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit			
DC perfo	DC performance								
-		SHDN = V _{IL}		5	50	nA			
I _{CC}	Supply current in shutdown mode (all operators)	$T_{min} < T_{op} < 85^{\circ} C$			200	nA			
		$T_{min} < T_{op} < 125^{\circ} C$			1.5	μΑ			
t _{on}	Amplifier turn-on time	$R_L = 5 \text{ k}\Omega, V_{out} = V_{CC-} \text{ to } V_{CC-} + 0.2 \text{ V}$		200		ns			
t _{off}	Amplifier turn-off time	$R_L = 5 k\Omega$, $V_{out} = V_{CC+} - 0.5 V$ to $V_{CC+} - 0.7 V$		20		ns			
V _{IH}	SHDN logic high		2			V			
V _{IL}	SHDN logic low				0.8	V			
I _{IH}	SHDN current high	SHDN = V _{CC+}		10		pА			
۱ _{IL}	SHDN current low	SHDN = V _{CC-}		10		pА			
	Output leakage in shutdown	SHDN = V _{CC-}		50		pА			
lOLeak	mode	T _{min} < T _{op} < 125° C		1		nA			



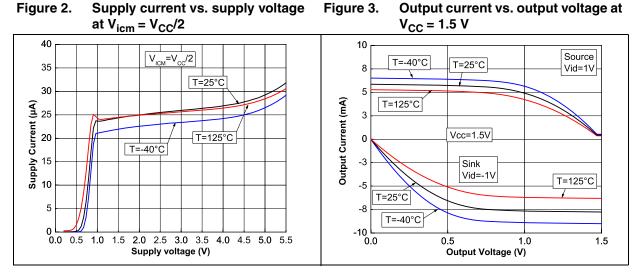
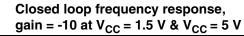


Figure 4. Output current vs. output voltage at Figure 5. $V_{CC} = 5 V$



Closed loop frequency response,

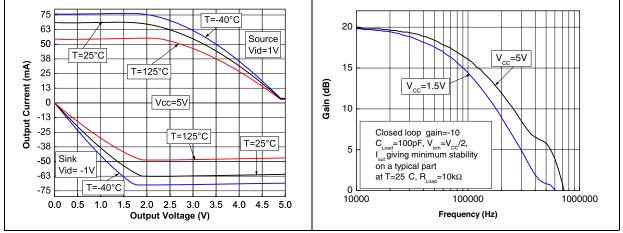
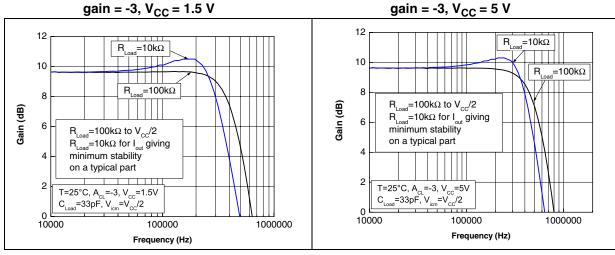


Figure 7.

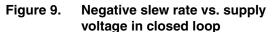
Figure 6. Closed loop frequency response, gain = -3, V_{CC} = 1.5 V



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Figure 8. Positive slew rate vs. supply voltage in closed loop



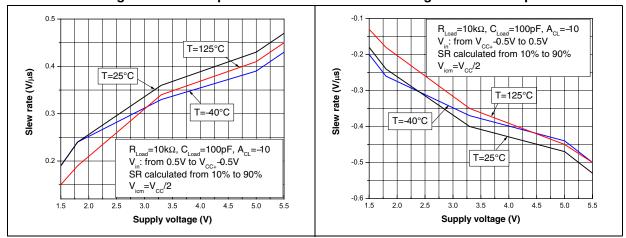
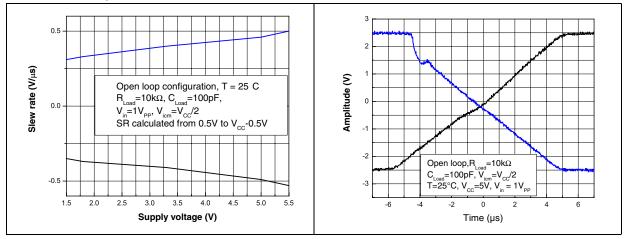
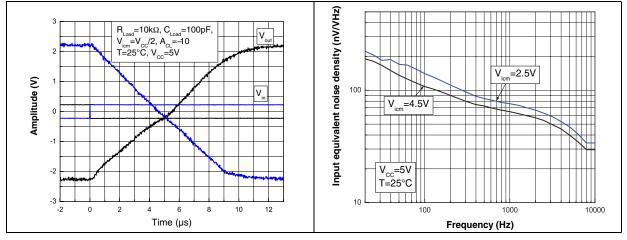


Figure 10. Slew rate vs. supply voltage in open Figure 11. Slew rate timing in open loop loop









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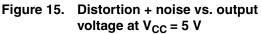
0.1

0.01

0.01

THD + N (%)

Figure 14. Distortion + noise vs. output voltage at V_{CC} = 1.8 V



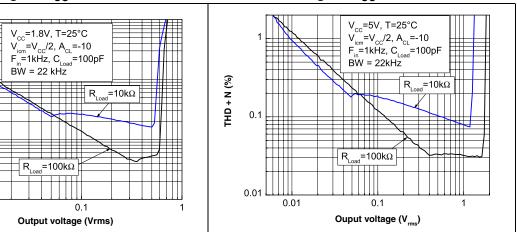


Figure 16. Distortion + noise vs. frequency at Figure 17. Distortion + noise vs. frequency at $V_{CC} = 1.8 V$ $V_{CC} = 5 V$

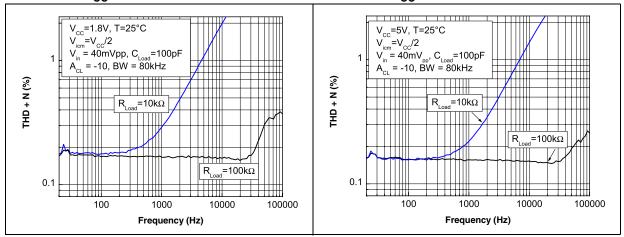
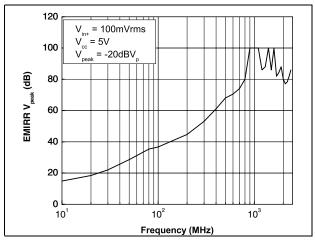


Figure 18. EMIRR vs. frequency at Vcc = 5 V, T = 25° C



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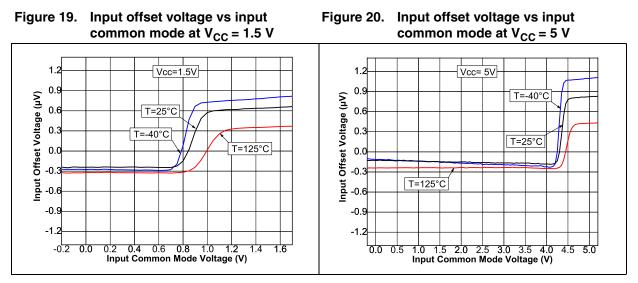
4 Application information

4.1 Operating voltages

The TSV629x can operate from 1.5 to 5.5 V. The devices' parameters are fully specified for 1.8, 3.3 and 5 V power supplies. However, the parameters are very stable in the full V_{CC} range and several characterization curves show the TSV629x characteristics at 1.5 V. Additionally, the main specifications are guaranteed in extended temperature ranges from -40° C to +125° C.

4.2 Rail-to-rail input

The TSV629x are built with two complementary PMOS and NMOS input differential pairs. The devices have a rail-to-rail input, and the input common mode range is extended from V_{CC-} - 0.1 V to V_{CC+} + 0.1 V. The transition between the two pairs appears at V_{CC+} - 0.7 V. In the transition region, the performance of CMR, SVR, V_{io} (*Figure 19* and *Figure 20*) and THD is slightly degraded.



The devices are guaranteed without phase reversal.

4.3 Rail-to-rail output

The operational amplifiers' output level can go close to the rails: 35 mV maximum above and below the rail when connected to a 10 k Ω resistive load to V_{CC}/2.



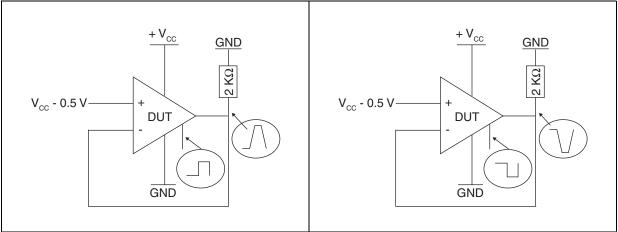
4.4 Optimization of DC and AC parameters

These devices use an innovative approach to reduce the spread of the main DC and AC parameters. An internal adjustment achieves a very narrow spread of current consumption (29 μ A typical, min/max at ±17%). Parameters linked to the current consumption value, such as GBP, SR and A_{vd} benefit from this narrow dispersion.

4.5 Shutdown function (TSV6293, TSV6295)

The operational amplifier is enabled when the \overline{SHDN} pin is pulled high. To disable the amplifier, the \overline{SHDN} must be pulled down to V_{CC^-} . When in shutdown mode, the amplifier output is in a high impedance state. The \overline{SHDN} pin must never be left floating but tied to V_{CC^+} or V_{CC^-} . The turn-on and turn-off times are calculated for an output variation of ± 200 mV (*Figure 21* and *Figure 22* show the test configurations).

Figure 21. Test configuration for turn-on time Figure 22. Test configuration for turn-off time (Vout pulled down) (Vout pulled down)



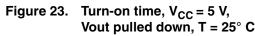
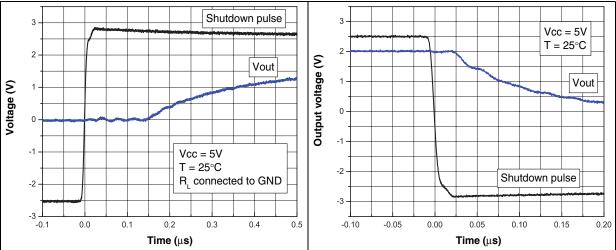


Figure 24. Turn-off time, $V_{CC} = 5 V$, Vout pulled down, $T = 25^{\circ} C$



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4.6 Driving resistive and capacitive loads

These products are micropower, low-voltage operational amplifiers optimized to drive rather large resistive loads, above 5 k Ω For lower resistive loads, the THD level may significantly increase.

The amplifiers have a relatively low internal compensation capacitor, making them very fast while consuming very little. They are ideal when used in a non-inverting configuration or in an inverting configuration in the following conditions:

- IGainl \geq 3 in an inverting configuration (C_L = 20 pF, R_L = 100 k Ω) or Igainl \geq 10 (C_L = 100 pF, R_L = 100 k Ω)
- Gain \geq +4 in a non-inverting configuration (C_L = 20 pF, R_L = 100k Ω) or gain \geq +11 (C_L = 100 pF, R_L= 100 k Ω)

As these operational amplifiers are not unity gain stable, the TSV62x (29 μ A, 420 kHz) or TSV63x (60 μ A, 880 kHz) – which are unity gain stable – might be a solution for your application.

Part #	lcc (µA) at 5V	GBP (MHz)	SR (V/µs)	Minimum gain for stability (C _{Load} = 100 pF)
TSV622-3-4-5	29	0.42	0.14	1
TSV6292-3-4-5	29	1.3	0.5	+11
TSV632-3-4-5	60	0.88	0.34	1
TSV6392-3-4-5	60	2.4	1.1	+11

Table 9. Related products

4.7 PCB layouts

For correct operation, it is advised to add 10 nF decoupling capacitors as close as possible to the power supply pins.

4.8 Macromodel

Two accurate macromodels (with or without shutdown feature) of the TSV629x are available on STMicroelectronics' web site at www.st.com. This model is a trade-off between accuracy and complexity (that is, time simulation) of the TSV629x operational amplifiers. It emulates the nominal performances of a typical device within the specified operating conditions mentioned in the datasheet. It also helps to validate a design approach and to select the right operational amplifier, but it does not replace on-board measurements.



5 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK[®] is an ST trademark.

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5.1 SOT23-8 package information

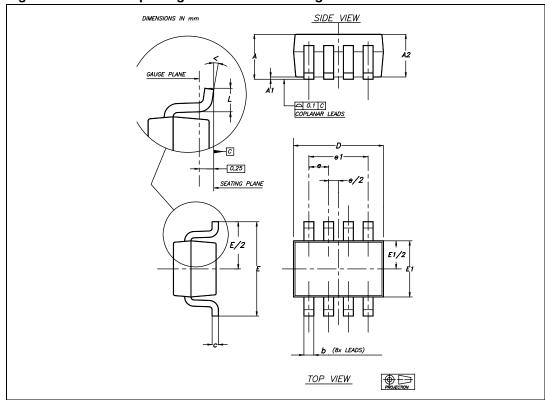


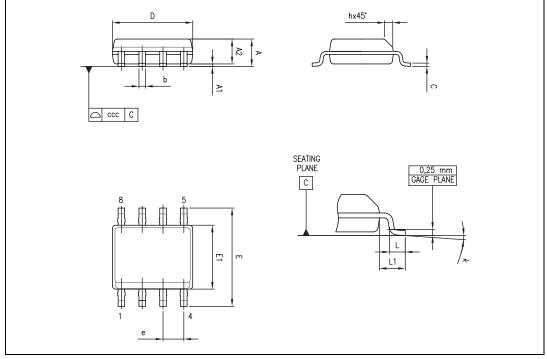
Figure 25. SOT23-8 package mechanical drawing

	Dimensions						
Ref.		Millimeters			Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max.	
А			1.45			0.057	
A1			0.15			0.006	
A2	0.90		1.30	0.035		0.051	
b	0.22		0.38	0.009		0.015	
С	0.08		0.22	0.003		0.009	
D	2.80		3	0.110		0.118	
Е	2.60		3	0.102		0.118	
E1	1.50		1.75	0.059		0.069	
е		0.65			0.026		
e1		1.95			0.077		
L	0.30		0.60	0.012		0.024	
<	0°		8°				



5.2 SO-8 package information





	Dimensions					
Ref.	Millimeters			Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max.
А			1.75			0.069
A1	0.10		0.25	0.004		0.010
A2	1.25			0.049		
b	0.28		0.48	0.011		0.019
С	0.17		0.23	0.007		0.010
D	4.80	4.90	5.00	0.189	0.193	0.197
Е	5.80	6.00	6.20	0.228	0.236	0.244
E1	3.80	3.90	4.00	0.150	0.154	0.157
е		1.27			0.050	
h	0.25		0.50	0.010		0.020
L	0.40		1.27	0.016		0.050
L1		1.04			0.040	
k	0		8°	1°		8°
CCC			0.10			0.004



5.3 MiniSO-8 package information

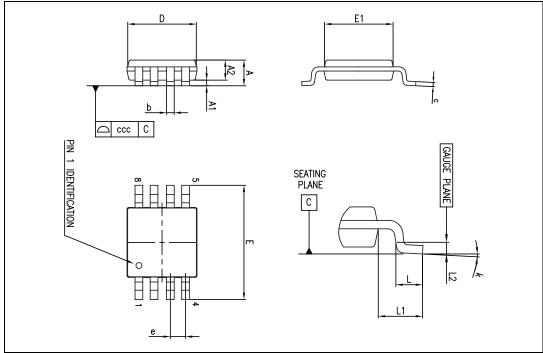


Figure 27. MiniSO-8 package mechanical drawing

Table 12. MiniSO-8 package mechanical data

	Dimensions						
Ref.	Millimeters			Inches			
	Min.	Тур.	Max.	Min.	Тур.	Max.	
А			1.1			0.043	
A1	0		0.15	0		0.006	
A2	0.75	0.85	0.95	0.030	0.033	0.037	
b	0.22		0.40	0.009		0.016	
С	0.08		0.23	0.003		0.009	
D	2.80	3.00	3.20	0.11	0.118	0.126	
E	4.65	4.90	5.15	0.183	0.193	0.203	
E1	2.80	3.00	3.10	0.11	0.118	0.122	
е		0.65			0.026		
L	0.40	0.60	0.80	0.016	0.024	0.031	
L1		0.95			0.037		
L2		0.25			0.010		
k	0°		8°	0°		8°	
ccc			0.10			0.004	



5.4 MiniSO-10 package information

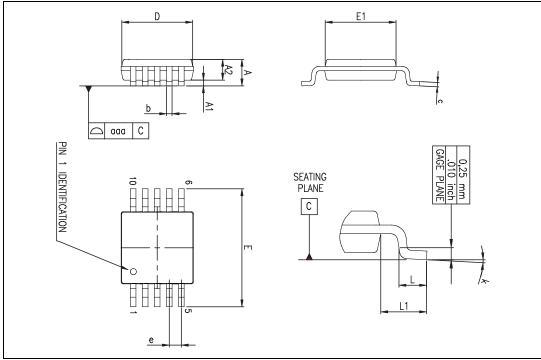


Figure 28. MiniSO-10 package mechanical drawing

Table 13. MiniSO-10 package mechanical data

	Dimensions						
Ref.	Millimeters			Inches			
	Min.	Тур.	Max.	Min.	Тур.	Max.	
А			1.10			0.043	
A1	0.05	0.10	0.15	0.002	0.004	0.006	
A2	0.78	0.86	0.94	0.031	0.034	0.037	
b	0.25	0.33	0.40	0.010	0.013	0.016	
с	0.15	0.23	0.30	0.006	0.009	0.012	
D	2.90	3.00	3.10	0.114	0.118	0.122	
E	4.75	4.90	5.05	0.187	0.193	0.199	
E1	2.90	3.00	3.10	0.114	0.118	0.122	
е		0.50			0.020		
L	0.40	0.55	0.70	0.016	0.022	0.028	
L1		0.95			0.037		
k	0°	3°	6°	0°	3°	6°	
aaa			0.10			0.004	



5.5 **TSSOP14** package information

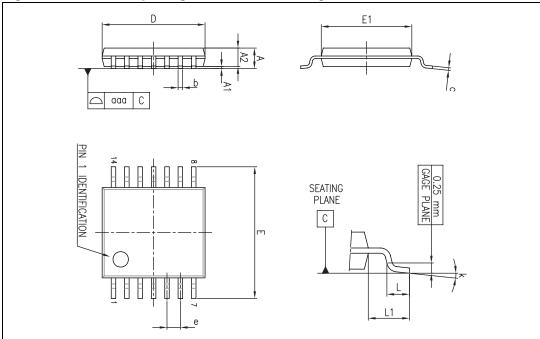


Figure 29. TSSOP14 package mechanical drawing

Table 14. TSSOP14 package mechanical data

	Dimensions							
Ref.		Millimeters			Inches			
	Min.	Тур.	Max.	Min.	Тур.	Max.		
А			1.20			0.047		
A1	0.05		0.15	0.002	0.004	0.006		
A2	0.80	1.00	1.05	0.031	0.039	0.041		
b	0.19		0.30	0.007		0.012		
С	0.09		0.20	0.004		0.0089		
D	4.90	5.00	5.10	0.193	0.197	0.201		
Е	6.20	6.40	6.60	0.244	0.252	0.260		
E1	4.30	4.40	4.50	0.169	0.173	0.176		
е		0.65			0.0256			
L	0.45	0.60	0.75	0.018	0.024	0.030		
L1		1.00			0.039			
k	0°		8°	0°		8°		
aaa			0.10			0.004		



5.6 TSSOP16 package information

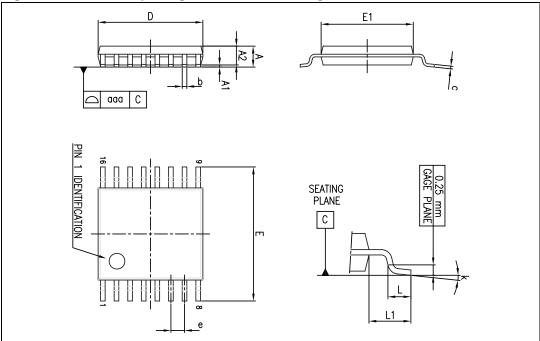


Figure 30. TSSOP16 package mechanical drawing

Table 15. TSSOP16 package mechanical data

	Dimensions						
Ref.		Millimeters			Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max.	
А			1.20			0.047	
A1	0.05		0.15	0.002		0.006	
A2	0.80	1.00	1.05	0.031	0.039	0.041	
b	0.19		0.30	0.007		0.012	
С	0.09		0.20	0.004		0.008	
D	4.90	5.00	5.10	0.193	0.197	0.201	
Е	6.20	6.40	6.60	0.244	0.252	0.260	
E1	4.30	4.40	4.50	0.169	0.173	0.177	
е		0.65			0.0256		
k	0°		8°	0°		8°	
L	0.45	0.60	0.75	0.018	0.024	0.030	
L1		1.00			0.039		
aaa			0.10			0.004	



6 Ordering information

Table 16.	Order codes
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Part number	Temperature range	Package	Packing	Marking
TSV6292ID/DT		SO-8	Tube and tape & reel	V6292I
TSV6292AID/DT		30-8	Tube and tape & reer	V6292AI
TSV6292IST		MiniCO 9		K114
TSV6292AIST		MiniSO-8	Tape & reel	K144
TSV6292ILT	-40° C to +125° C	SOT23-8	Tape & reel	K114
TSV6293IST		Mini00 10	Tape & reel	K134
TSV6293AIST		MiniSO-10		K135
TSV6294IPT		T000D 14		V6294
TSV6294AIPT		TSSOP-14	Tape & reel	V6294A
TSV6295IPT		T000D 10		V6295
TSV6295AIPT		TSSOP-16	Tape & reel	V6295A



7 Revision history

Table 17.Document revision history

Date	Revision	Changes
14-Jan-2010	1	Initial release.
01-Mar-2010	2	Corrected error in <i>Table 16: Order codes</i> : TSV6295 offered in TSSOP-16 package.

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